

12/28/01

01-04-02

PATENT
Docket No: ACT-307DVA

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: Not yet assigned

Examiner: Not yet assigned

Serial No. Not yet assigned

Filed: December 28, 2001

In re Application of: Hawley et al.

For: METHOD FOR FABRICATING A MOS TRANSISTOR HAVING IMPROVED
TOTAL RADIATION-INDUCED LEAKAGE CURRENT

j1002 U.S. PRO
10/036303

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I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as Express Mailing Label No. EL858979185US, in an envelope addressed to Director of Patents, Box New Application, Washington, D.C. 20231
on 12/28/01, Signed John M. Dillman

CONTINUING APPLICATION TRANSMITTAL LETTER
37 C.F.R. § 1.53(b)

Director of Patents
Box New Application
Washington, D.C. 20231

Dear Sir:

This is a request for filing under the Continuing Application Procedure, 37 C.F.R. § 1.53(b); for a divisional application of prior application Serial No. 09/741,949, filed December 20, 2000, naming inventors Frank Hawley and Daniel Wang. The prior application is assigned of record to Actel Corporation. Enclosed for filing are 12 pages specification, 3 pages of claims, 4 sheets drawings and one page abstract. Also enclosed is a Preliminary Amendment and a Request for Non-Publication.

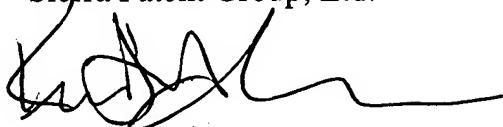
The attorney's Docket Number of this application is ACT-307DVA.

Kindly address all communications regarding this application to:

Kenneth D'Alessandro
Sierra Patent Group, Ltd.
P.O. Box 6149
Stateline, NV 89449
(775) 586-9500

No fee is being paid at this time.

Respectfully submitted,
Sierra Patent Group, Ltd.



Kenneth D'Alessandro
Reg. No. 29,144

Sierra Patent Group, Ltd.
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DECEMBER 28, 2001

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on 12/28/01, Signed 

Stephanie Davis

REQUEST FOR NONPUBLICATION PURSUANT TO 37 C.F.R. § 1.213

Director of Patents
Washington, D.C. 20231

Sir:

Applicant hereby requests that this application not be published under 35 U.S.C. §122(b). Applicant certifies that the invention disclosed in the application has not been and will not be the subject of an application filed in another country, or under a multilateral agreement, that requires publication at eighteen months after filing.

Respectfully submitted,
Sierra Patent Group, Ltd.



Kenneth D'Alessandro
Reg. No.: 29,144

Dated: December 28, 2001

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